

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Surface-mounted package
- ☒ Advanced trench cell design

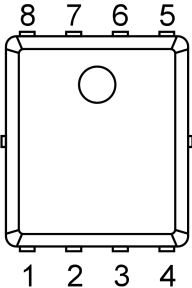
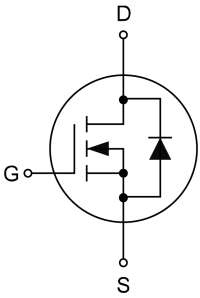
1.2 Applications

- ☒ Motor appliances
- ☒ High power inverter system

1.3 Quick reference

- ☒ $BV \geq 30\text{ V}$
- ☒ $P_{tot} \leq 35\text{ W}$
- ☒ $I_D \leq 80\text{ A}$
- ☒ $R_{DS(ON)} \leq 7\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☒ $R_{DS(ON)} \leq 9\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 Top View PDFN5x6-8L	
4	Gate		
5,6,7,8	Drain		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	30	-	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
I_D	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	80	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	57.5	A
I_{DM}^*	Pulsed Source Current	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	180	A
P_{tot}	Total Power Dissipation	$T_C=25^{\circ}\text{C}$	-	35	W
I_S	Diode Forward Current	$T_C=25^{\circ}\text{C}$	-	80	A
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		-	62.5	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance-Junction to Case		-	3.5	$^{\circ}\text{C}/\text{W}$

Notes:

- * Surface Mounted on 1 in² pad area, $t \leq 10\text{ sec}$.
- ** Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- *** Limited by bonding wire.

4. Marking Information

Product Name	Marking
KJ0603G	0603 XXXXXX

5. Ordering Code

Product Name	Package	Reel size	Tape width	Quantity (pcs)
KJ0603G	PDFN 5x6-8L	13"	12 mm	5000

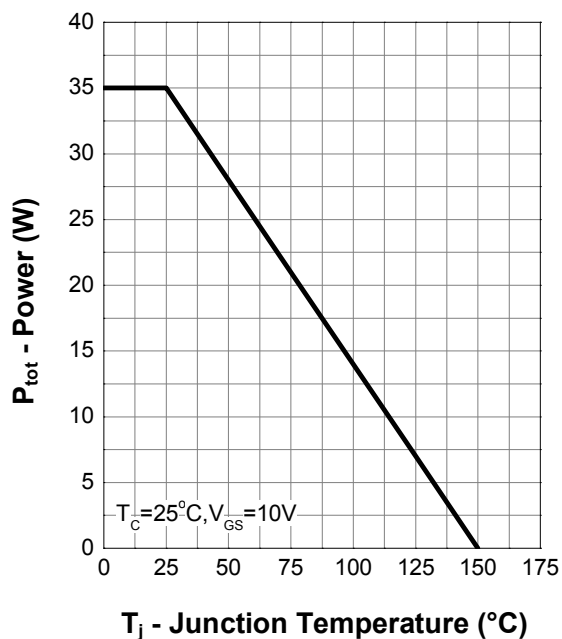
Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

6. Electrical Characteristics (T_A=25°C unless otherwise noted)

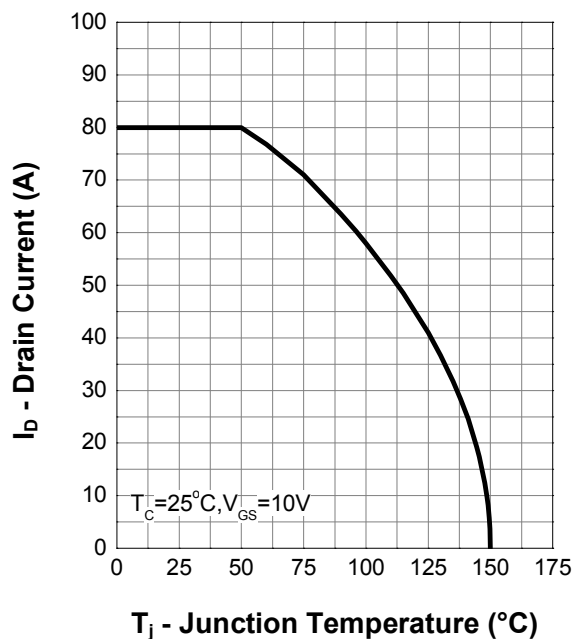
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	30	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	1	-	2	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24 V, V _{GS} =0 V	-	-	1	μA
		T _J =85°C	-	-	±30	μA
I _{GSS}	Gate Leakage Current	V _{DS} =0 V, V _{GS} =±20 V	-	-	±100	nA
R _{DS(ON)}	On-State Resistance	V _{GS} =10 V, I _{DS} =10 A	-	6	7	mΩ
		V _{GS} =4.5 V, I _{DS} =5 A	-	8.5	9	
Diode Characteristics						
V _{SD}	Diode Forward Voltage	I _{SD} =10 A, V _{GS} =0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{DS} =10 A, V _{GS} =0 V, dI _{SD} /dt=100 A/μs	-	34	-	ns
Q _{rr}	Reverse Recovery Charge		-	7.1	-	nC
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =15 V, f=1 MHz	-	1145	-	pF
C _{oss}	Output Capacitance		-	106	-	
C _{rss}	Reverse Transfer Capacitance		-	87	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =15 V, V _{GEN} =10 V, R _G =4.5 Ω, R _L =1.5 Ω, I _{DS} =10 A	-	7	-	ns
t _r	Turn-on Rise Time		-	30	-	
t _{d(off)}	Turn-off Delay Time		-	19	-	
t _f	Turn-off Fall Time		-	18	-	
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} =15 V, V _{GS} =10 V, I _{DS} =10 A	-	22	-	nC
Q _{gs}	Gate-Source Charge		-	5	-	
Q _{gd}	Gate-Drain Charge		-	3.3	-	

7. Typical Characteristics

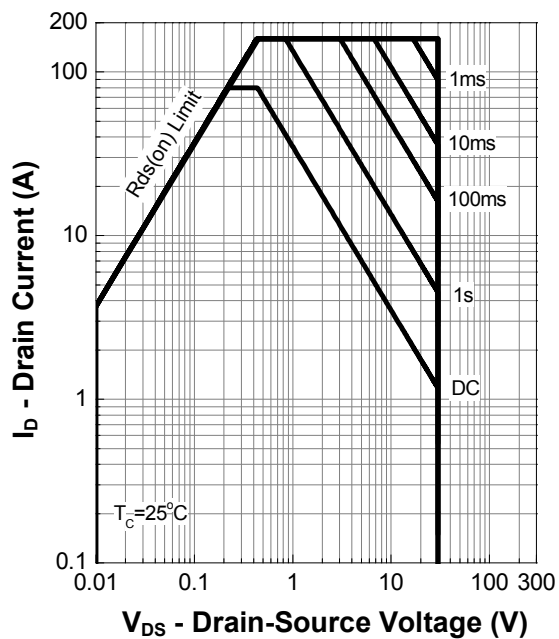
Power Capability



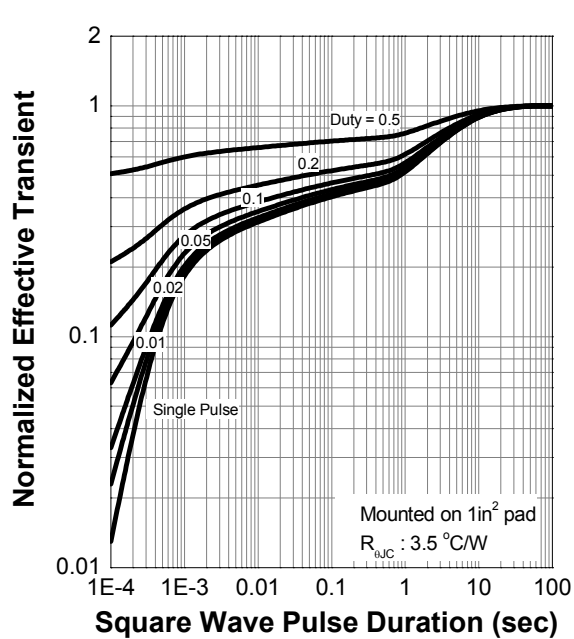
Current Capability



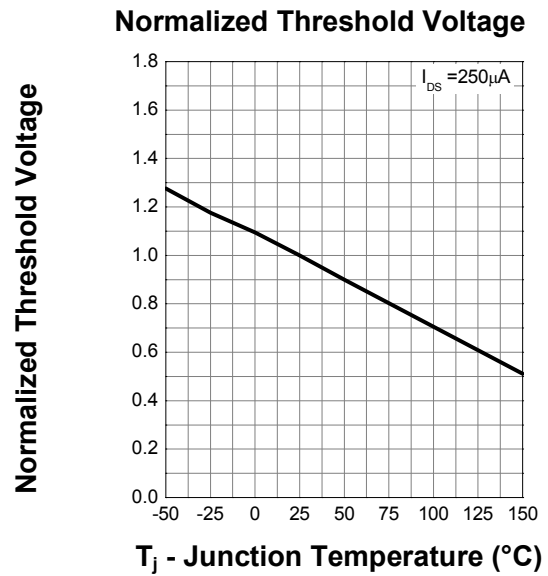
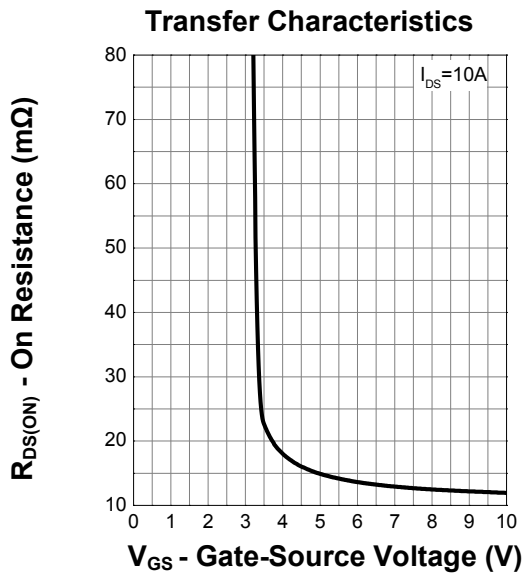
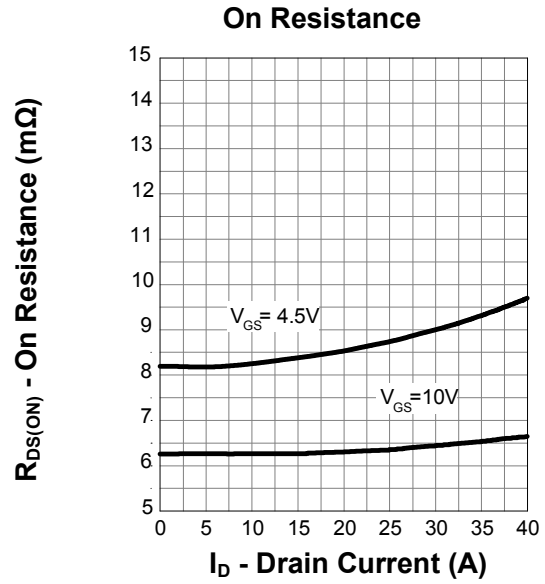
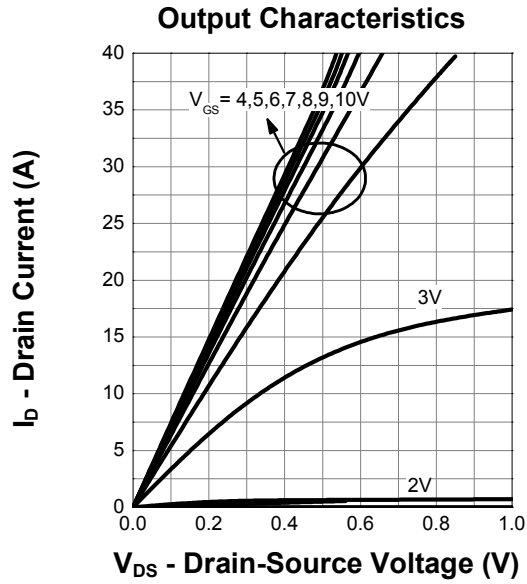
Safe Operation Area



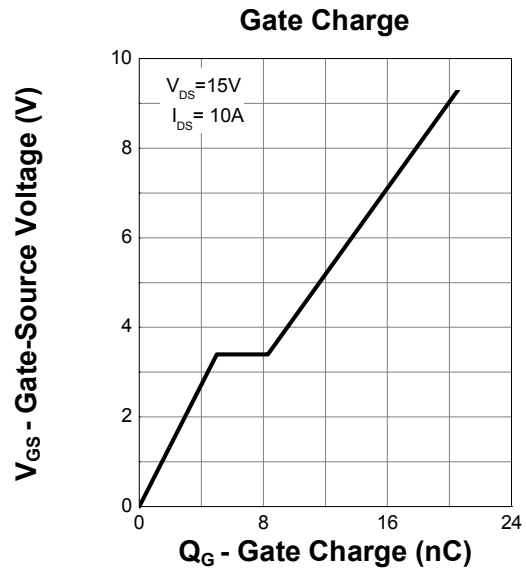
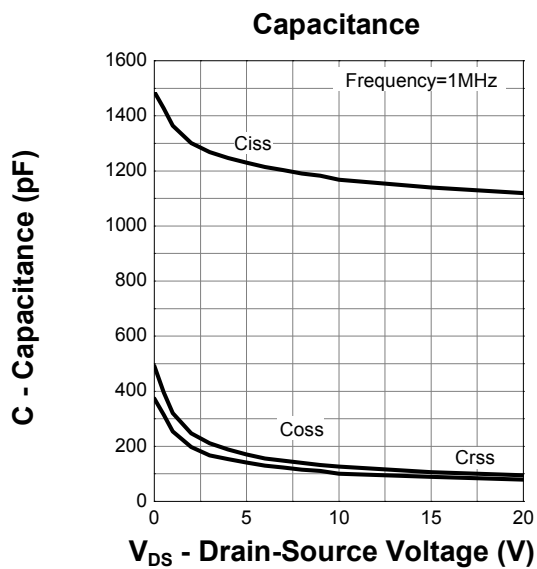
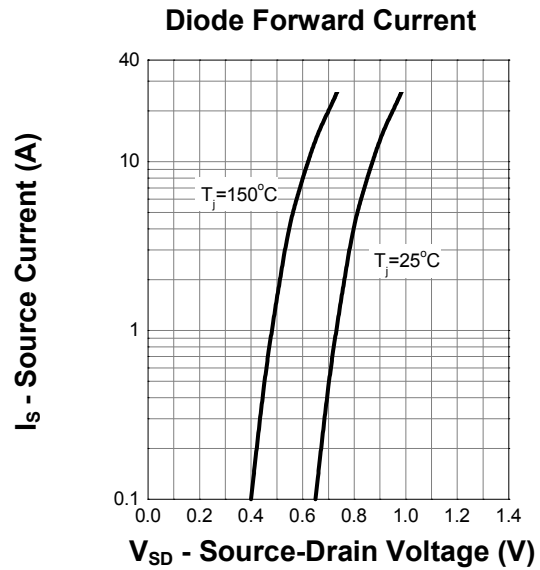
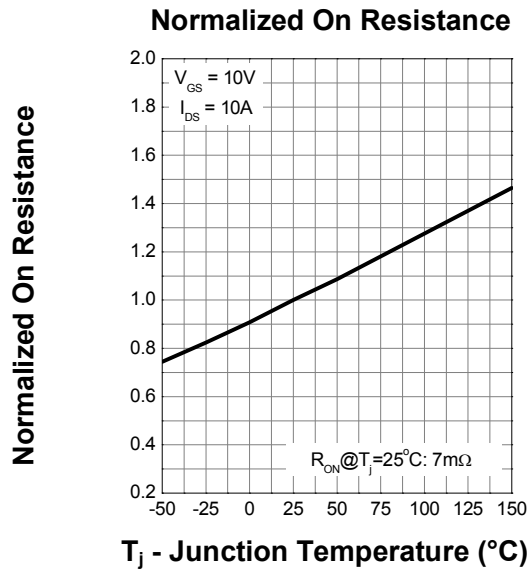
Transient Thermal Impedance



7. Typical Characteristics (cont.)



7. Typical Characteristics (cont.)



8. Package Dimensions

PDFN5x6-8L Package

